UTC UNISONIC TECHNOLOGIES CO., LTD

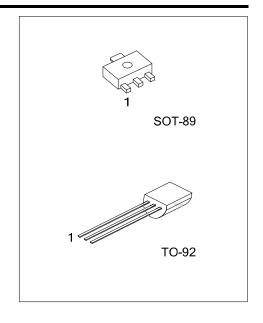
MJE13001

NPN SILICON TRANSISTOR

NPN SILICON POWER TRANSISTOR

FEATURES

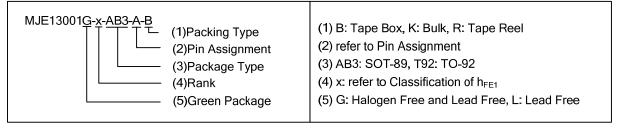
- * Collector-base voltage: V(BR)CBO=600V
- * Collector current: I_C=0.2A



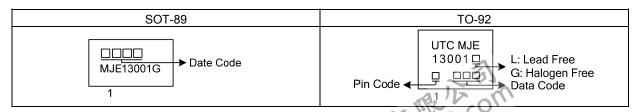
ORDERING INFORMATION

Ordering	<u> </u>	Pin	Assignm	5			
Lead Free	Halogen Free	Package	1	2	3	Packing	
-	MJE13001G-x-AB3-A-R	SOT-89	Е	С	В	Tape Reel	
-	MJE13001G-x-AB3-F-R	SOT-89	В	С	Е	Tape Reel	
MJE13001L-x-T92-B	MJE13001G-x-T92-B	TO-92	В	С	Е	Tape Box	
MJE13001L-x-T92-K	MJE13001G-x-T92-K	TO-92	В	С	Е	Bulk	
MJE13001L-x-T92-A-B	MJE13001G-x-T92-A-B	TO-92	Е	С	В	Tape Box	
MJE13001L-x-T92-A-K	MJE13001G-x-T92-A-K	TO-92	E	С	В	Bulk	

Pin Assignment: C: Collector B: Base E: Emitter



MARKING



www.unisonic.com.tw 1 of 3 QW-R201-055.I

ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V_{CEO}	400	V
Collector-Base Voltage		V_{CBO}	600	V
Emitter Base Voltage		V_{EBO}	7	٧
Collector Current		Ic	200	mA
Callastan Dayyan Dissination	SOT-89		550	10/200
Collector Power Dissipation	TO-92	P _C	750	mW
Junction Temperature		T_J	+150	Ŝ
Storage Temperature		T _{STG}	-55 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

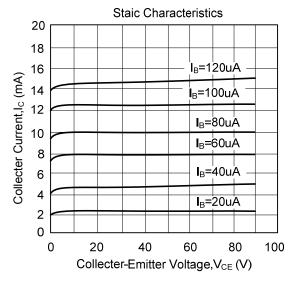
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	600			V			
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	400			V			
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =100μA, I _C =0	7			V			
Base-Emitter Voltage	V_{BE}	I _E =100 mA			1.1	V			
Collector Cutoff Cut-Off Current	I _{CBO}	V _{CB} =600V, I _E =0A			100	μA			
Collector Emitter Cut-Off Current	I _{CEO}	V _{CE} =400V, I _B =0			200	μA			
Emitter Cutoff Cut-Off Current	I _{EBO}	V _{EB} =7V, I _C =0A			100	μA			
ON CHARACTERISTICS									
DC Commant Cain	h _{FE1} *	V _{CE} =20 V, I _C =20mA	10		70				
DC Current Gain	h _{FE2}	V _{CE} =10V, I _C =0.25mA	5						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =50mA, I _B =10mA			0.5	V			
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =50mA, I _B =10mA			1.2	V			
SMALL-SIGNAL CHARACTERISTICS									
Current Gain Bandwidth Product	f⊤	I _C =20mA,V _{CE} =20V,f=1MHz	8			MHz			
Resistive Load									
Storage Time	ts	I _C =50mA, I _{B1} =-I _{B2} =5mA,			1.5	μs			
Fall Time	t _F	V _{CC} =45V			0.3	μs			

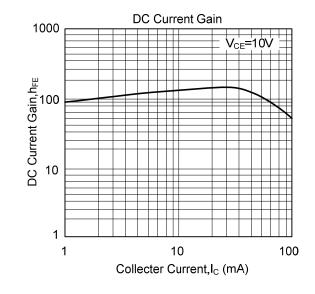
CLASSIFICATION OF h_{FE1}*

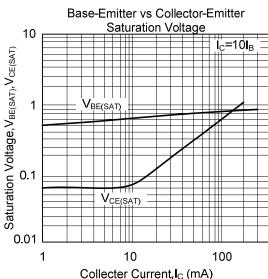
RANK	Α	В	С	D	Е	F	G	Η	I	J	K	L
RANGE	10-15	15-20	20-25	25-30	30-35	35-40	40-45	45-50	50-55	55-60	60-65	65-70

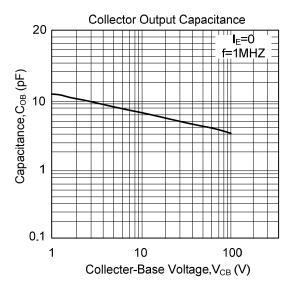


■ TYPICAL CHARACTERISTICS









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